

Title (en)  
Method for manufacturing a lithium ion-conductor

Title (de)  
Verfahren zur Herstellung eines Lithiumionenleiters

Title (fr)  
Procédé de fabrication de conducteur d'ions lithium

Publication  
**EP 1431423 A1 20040623 (DE)**

Application  
**EP 03026513 A 20031118**

Priority  
DE 10259022 A 20021216

Abstract (en)  
A solid lithium ion conductor is prepared by shaping and calcining a lithium compound and/or compounds that are converted into this during calcination and in the form of powder having a mean particle size of not more than 5 µm. Preparation of a solid lithium ion conductor having a composition  $\text{Li}_{4-x}\text{Si}_{1-x}\text{PxO}_4$  involves shaping and calcining  $\text{Li}_{4-x}\text{Si}_{1-x}\text{PxO}_4$  and/or compounds that are converted into this during calcination. The  $\text{Li}_{4-x}\text{Si}_{1-x}\text{PxO}_4$  and/or compounds is/are used in the form of powder having a mean particle size of not more than 5 µm.  $x =$  at least 0.3 and not more than 0.7.

Abstract (de)  
Ein Lithiumionenleiter der Zusammensetzung  $\text{Li}_{4-x}\text{Si}_{1-x}\text{PxO}_4$ , wobei  $x$  einen Wert von mindestens 0,3 und höchstens 0,7 hat, wird durch Verformen und Kalzinieren von  $\text{Li}_{4-x}\text{Si}_{1-x}\text{PxO}_4$ , wobei  $x$  einen Wert von mindestens 0,3 und höchstens 0,7 hat und/oder von Verbindungen, die sich während der Kalzination dazu umsetzen, hergestellt, wobei das  $\text{Li}_{4-x}\text{Si}_{1-x}\text{PxO}_4$  und/oder die Verbindungen in Form von Pulver mit einer mittleren Partikelgröße von höchstens 5 Mikrometern verwendet werden.

IPC 1-7  
**C25C 7/04**; **C25C 3/02**; **C22B 26/12**

IPC 8 full level  
**C04B 35/447** (2006.01); **C01B 33/32** (2006.01); **C04B 35/16** (2006.01); **C22B 26/12** (2006.01); **C25C 3/02** (2006.01); **C25C 7/04** (2006.01)

CPC (source: EP US)  
**C22B 26/12** (2013.01 - EP US); **C25C 3/02** (2013.01 - EP US); **C25C 7/04** (2013.01 - EP US); **Y10T 29/49108** (2015.01 - EP US)

Citation (search report)

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